

**CMSD2836**  
**CMSD2838**

**NEW**

**SUPER-MINI**  
**DUAL SILICON**  
**SWITCHING DIODE**

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**SUPER**<sup>TM</sup>  
**mini**



**SOT-323 CASE**

**DESCRIPTION**

The CENTRAL SEMICONDUCTOR CMSD2836, CMSD2838 types are ultra-high speed silicon switching diodes manufactured by the epitaxial planar process, in an epoxy molded super-mini surface mount package, designed for high speed switching applications.

The following configurations are available:

CMSD2836  
CMSD2838

DUAL, COMMON ANODE  
DUAL, COMMON CATHODE

MARKING CODE: A2C  
MARKING CODE: A6C

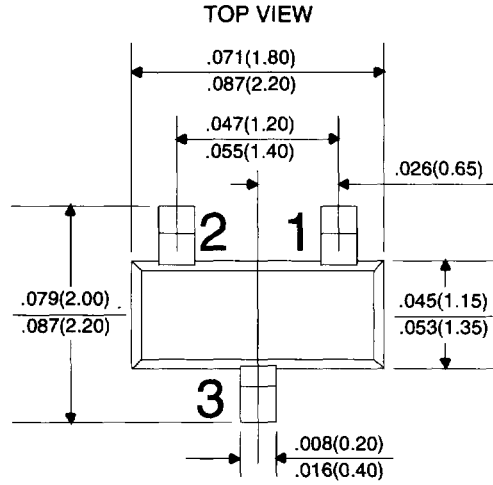
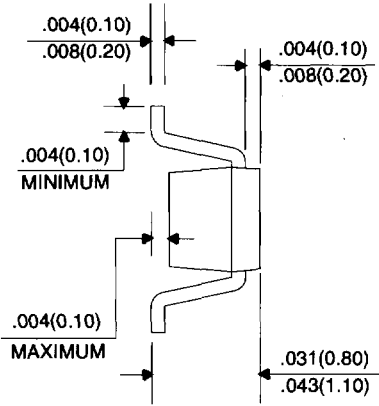
**MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	75	V
Average Forward Current	$I_O$	200	mA
Peak Forward Current	$I_{FM}$	300	mA
Power Dissipation Operating and Storage	$P_D$	250	mW
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	500	$^\circ\text{C/W}$

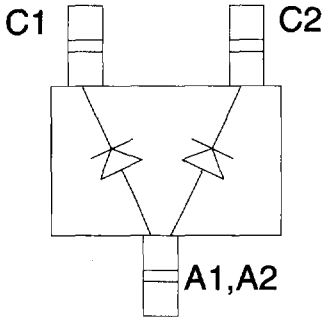
**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$BV_R$	$I_R=100\mu\text{A}$	75			V
$I_R$	$V_R=50\text{V}$			100	nA
$V_F$	$I_F=10\text{mA}$			1.0	V
$V_F$	$I_F=50\text{mA}$			1.0	V
$V_F$	$I_F=100\text{mA}$			1.2	V
$C_T$	$V_R=0, f=1\text{ MHz}$		1.5	6.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$			4.0	ns

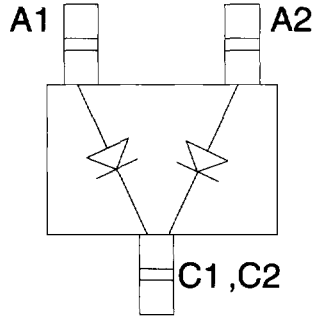
All dimensions in inches (mm).



Lead Code



CMSD2836



CMSD2838

DATA SHEET